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Search Results - Record(s) 1 through 6 of 6 returned.

1. Document ID: US 6383942 B1

L4: Entry 1 of 6

File: USPT

May 7, 2002

US-PAT-NO: 6383942

DOCUMENT-IDENTIFIER: US 6383942 B1

TITLE: Dry etching method

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments |

KWIC

2. Document ID: US 5963812 A

L4: Entry 2 of 6

File: USPT

Oct 5, 1999

US-PAT-NO: 5963812

DOCUMENT-IDENTIFIER: US 5963812 A

TITLE: Manufacturing method of a semiconductor apparatus having an

electron donative surface in a side wall portion

Full Title Citation Front Review Classification Date Reference Sequences Attachments Draw, Desc Image

3. Document ID: US 5580808 A

L4: Entry 3 of 6

File: USPT

Dec 3, 1996

US-PAT-NO: 5580808

DOCUMENT-IDENTIFIER: US 5580808 A

TITLE: Method of manufacturing a ROM device having contact holes treated with hydrogen atoms and energy beam

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Draw Desc Image

4. Document ID: US 5569614 A

L4: Entry 4 of 6 File: USPT

Oct 29, 1996

US-PAT-NO: 5569614

DOCUMENT-IDENTIFIER: US 5569614 A

TITLE: Method of forming metal pattern including a schottky diode

Full Title Citation Front Review Classification Date Reference Sequences Attachiments Draw Desc Image

5. Document ID US 5527730 A

L4: Entry 5 of 6 File: USPT

Jun 18, 1996

US-PAT-NO: 5527730

DOCUMENT-IDENTIFIER: US 5527730 A

TITLE: Method of forming a capacitor having contact hole treated

with hydrogen atoms and energy beam



6. Document ID: US 5393565 A

L4: Entry 6 of 6 File: USPT

Feb 28, 1995

US-PAT-NO: 5393565

DOCUMENT-IDENTIFIER: US 5393565 A

TITLE: Method for deposition of a refractory metal nitride and method for formation of a conductive film containing a refractory metal nitride

Full Title Citation Front Review Classification Date Reference Sequences Attachments Draw. Desc Image

KOMC

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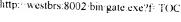
Terms **Documents** L1 and (reactive adj gases)

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Previous Page

Next Page



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Search Results - Record(s) 1 through 10 of 27 returned.

1. Document ID: US 6500742 B1

L9: Entry 1 of 27

File: USPT

Dec 31, 2002

US-PAT-NO: 6500742

DOCUMENT-IDENTIFIER: US 6500742 B1

TITLE: Construction of a film on a semiconductor wafer

Full Title Citation Front Review Classification Date Reference Sequences Attachments

2. Document ID: US 6495458 B2

L9: Entry 2 of 27

File: USPT

Dec 17, 2002

US-PAT-NO: 6495458

DOCUMENT-IDENTIFIER: US 6495458 B2

TITLE: Method for producing low carbon/oxygen conductive layers

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Draww Desc | Image

3. Document ID: US 6491978 B1

L9: Entry 3 of 27

File: USPT

Dec 10, 2002

US-PAT-NO: 6491978

DOCUMENT-IDENTIFIER: US 6491978 B1

TITLE: Deposition of CVD layers for copper metallization using novel metal organic chemical vapor deposition (MOCVD) precursors

Full Title Citation Front Review Classification Date Reference Sequences Attachments Draw Desc Image

4. Document ID: US 6465345 B1

L9: Entry 4 of 27 File: USPT

Oct 15, 2002

US-PAT-NO: 6465345

DOCUMENT-IDENTIFIER: US 6465345 B1

TITLE: Prevention of inter-channel current leakage in

semiconductors

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Drawu Desc Image

5. Document ID: US 6451692 B1

L9: Entry 5 of 27 File: USPT

Sep 17, 2002

US-PAT-NO: 6451692

DOCUMENT-IDENTIFIER: US 6451692 B1

TITLE: Preheating of chemical vapor deposition precursors

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments Draw, Desc Image

6. Document ID: US 6448187 B2

L9: Entry 6 of 27 File: USPT

Sep 10, 2002

US-PAT-NO: 6448187

DOCUMENT-IDENTIFIER: US 6448187 B2

TITLE: Method of improving moisture resistance of low dielectric

constant films

Full Title Citation Front Review Classification Date Reference Sequences Attachments Drawi Desc Image

KWAC

7 Document ID: US 6444542 B2

L9: Entry 7 of 27 File: USPT

Sep 3, 2002

US-PAT-NO: 6444542

DOCUMENT-IDENTIFIER: US 6444542 B2

TITLE: Integrated circuit and method

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Draws Desc Image

8. Document ID: US 6444036 B2

L9: Entry 8 of 27 File: USPT

Sep 3, 2002

US-PAT-NO: 6444036

DOCUMENT-IDENTIFIER: US 6444036 B2

TITLE: Construction of a film on a semiconductor wafer

Full Title Citation Front Review Classification Date Reference Sequences Attachments KOMC Draw, Desc - Image

9. Document ID: US 6403414 B2

L9: Entry 9 of 27

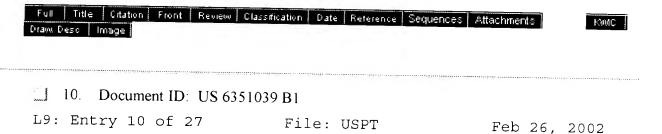
File: USPT

Jun 11, 2002

US-PAT-NO: 6403414

DOCUMENT-IDENTIFIER: US 6403414 B2

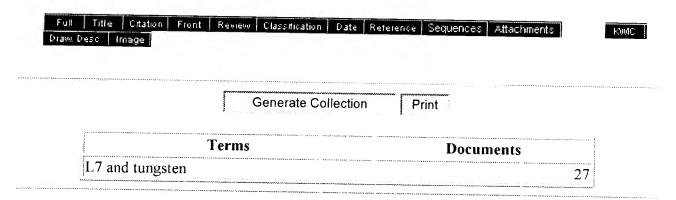
TITLE: Method for producing low carbon/oxygen conductive layers



US-PAT-NO: 6351039

DOCUMENT-IDENTIFIER: US 6351039 B1

TITLE: Integrated circuit dielectric and method



Display Format: TI Change Format

> Previous Page Next Page

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<u>L9</u>	L7 and tungsten	27	<u>L9</u>
<u>L8</u>	L7 and 438/.\$.clss.	0	<u>L8</u>
<u>L7</u>	L5 and silane	29	<u>L7</u>
<u>L6</u>	L5 and (stacked near barrier)	0	<u>L6</u>
<u>L5</u>	(Barrier adj layer) and (adhesion adj layer) and (copper) and ((reactive adj gases) or TDMAT or TDEAT or TiCl4)	68	<u>L5</u>
<u>L4</u>	L1 and (reactive adj gases)	6	<u>L4</u>
<u>L3</u>	L1 and (adhesion near layer)	3	<u>L3</u>
<u>L2</u>	L1 near7 adhesion	0	<u>L2</u>
<u>L1</u>	stacked near2 barrier	220	<u>L1</u>

END OF SEARCH HISTORY

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Search Results - Record(s) 1 through 3 of 3 returned.

1. Document ID: US 6447826 B1

L3: Entry 1 of 3

File: USPT

Sep 10, 2002

US-PAT-NO: 6447826

DOCUMENT-IDENTIFIER: US 6447826 B1

TITLE: Packaging for meat and foodstuff

Full Title Citation Front Review Classification Date Reference Sequences Attachments Claims KMC Draw, Desc Image

2. Document ID: US 6284595 B1

L3: Entry 2 of 3

File: USPT

Sep 4, 2001

US-PAT-NO: 6284595

DOCUMENT-IDENTIFIER: US 6284595 B1

TITLE: Method for fabricating stacked capacitor having excellent

anti-oxidation property

Full Title Citation Front Review Classification Date Reference Sequences Attachments Claims KMC Draw, Desc - Image

3. Document ID: US 6228701 B1

L3: Entry 3 of 3

File: USPT

May 8, 2001

US-PAT-NO: 6228701

DOCUMENT-IDENTIFIER: US 6228701 B1

TITLE: Apparatus and method for minimizing diffusion in stacked

capacitors formed on silicon plugs

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Draw Desc Image

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Terms	Documents
L1 and (adhesion near layer)	2 -

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Previous Page Next Page